

Form PTO 1449 (Modified)		U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE		ATTY DOCKET NO. 263878US2PCT		SERIAL NO. 101517772 New U.S. PCT Application Based on PCT/JP03/08146	
LIST OF REFERENCES CITED BY APPLICANT				APPLICANT Kenji FUKUDA, et al.			
				FILING DATE Herewith 12/27/04		GROUP 2812	
U.S. PATENT DOCUMENTS							
EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
	AA						
	AB						
	AC						
	AD						
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	AI						
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FOREIGN PATENT DOCUMENTS							
		DOCUMENT NUMBER	DATE	COUNTRY	TRANSLATION YES NO		
/WL/	AO	11-297712	10/29/99	JP(English abstract only)			NO
/WL/	AP	11-31691	02/02/99	JP(English abstract only)			NO
/WL/	AQ	2000-252461	09/14/00	JP(English abstract only)			NO
/WL/	AR	11-74263	03/16/99	JP(English abstract only)			NO
/WL/	AS	10-50701	02/20/98	JP(English abstract only)			NO
/WL/	AT	00/13236	03/09/00	WO			NO
/WL/	AU	9-199497	07/31/97	JP(English abstract only)			NO
/WL/	AV	10-112460	04/28/98	JP(English abstract only)			NO
OTHER REFERENCES (Including Author, Title, Date, Pertinent Pages, etc.)							
	AW						
	AX						
	AY						
	AZ						<input type="checkbox"/> Additional References sheet(s) attached
Examiner /Walter Lindsay Jr/					Date Considered 09/27/2007		
*Examiner: Initial if reference is considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.							

Form PTO 1449
(Modified)U.S. DEPARTMENT OF COMMERCE
PATENT AND TRADEMARK OFFICEATTY DOCKET NO.
263878US2PCTSERIAL NO.
10/517,772

LIST OF REFERENCES CITED BY APPLICANT

APPLICANT

Kenji FUKUDA, et al.

FILING DATE

December 27, 2004

GROUP

28/2

U.S. PATENT DOCUMENTS

EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
/WL/	AA	6 759 684	07/06/04	FUKUDA, Kenji et al.			
/WL/	AB	6 764 963	07/20/04	FUKUDA, Kenji et al.			
/WL/	AC	6 812 102	11/02/04	FUKUDA, Kenji et al.			
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	AN						

FOREIGN PATENT DOCUMENTS

		DOCUMENT NUMBER	DATE	COUNTRY	TRANSLATION YES NO	
/WL/	AO	2000-252461	09/14/00	JP (with English abstract & computer generated translation)		NO
/WL/	AP	11-031691	02/02/99	JP (with English abstract & computer generated translation)		NO
/WL/	AQ	09-199497	07/31/97	JP (with English abstract & computer generated translation)		NO
/WL/	AR	10-112460	04/28/98	JP (with English abstract & computer generated translation)		NO
	AS					
	AT					
	AU					
	AV					

OTHER REFERENCES (Including Author, Title, Date, Pertinent Pages, etc.)

/WL/	AW	OGINO, Shinji et al. "Channel Doped SiC-MOSFETs", Materials Science Forum, vols. 338-342, pages 1101-1104 2000				
/WL/	AX	FUKUDA, K. et al. "Effect of oxidation method and post-oxidation annealing on interface properties of metal-oxide-semiconductor structures formed on n-type 4H-SiC C(0001) face", Applied Physics Letters, vol. 77, no. 6, pages 866-868 2000				
	AY					
	AZ				<input type="checkbox"/> Additional References sheet(s) attached	

Examiner /Walter Lindsay Jr/

Date Considered 09/27/2007

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08/28/07

	Docket No.: 263878US2PCT	Serial No.: 10/517,772
LIST OF RELATED CASES CITED BY APPLICANT UNDER 37 CFR 1.56	Inventor: Kenji FUKUDA, et al.	
	Filing Date: July 12, 2005	Group: 2812

LIST OF RELATED CASES

Examiner <u>Initial</u>	<u>Docket No.</u>	Serial or <u>Patent Number</u>	Filing or <u>Issue Date</u>	Patent App. <u>Publication No.</u>	Inventor or <u>Applicant</u>
/WL/	263878US2PCT*	10/517,772	07/12/05	2005-0245034	FUKUDA, et al.
/WL/	307205US2PCT	11/718,036	04/26/07		YATSUO, et al.

Examiner

Date Considered

/Walter Lindsay Jr/

09/27/2007

*Present Application; listed for information

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